Democratic elections judge.

Mrs. Hiteshew, an accomplished seamstress who stitched many christening gowns and First Communion dresses, did free alterations for those who could not afford to pay. She also loved the Orioles, classical music and reading.

A Mass of Christian burial was offered Friday at Our Lady of Victory Roman Catholic Church in Arbutus, where Mrs. Hiteshew was a parishioner.

In addition to her son, she is survived by eight other sons, William Dorsey Hiteshew Jr. of Joppa, F. Donald Hiteshew of Baytown, Texas, Milton D. Hiteshew of Pasadena, John D. Hiteshew of Catonsville, Stephen C. Hiteshew of Phoenix, Ariz., Herbert F. Hiteshew of Baltimore, and Charles E. Hiteshew and Walter C. Hiteshew, both of **Ellicott City**; a daughter, H. Louise Lawson of **Ellicott City**; 35 grandchildren and 24 great-grandchildren.

Mrs. Hiteshew also was preceded in death by a daughter, Virginia A. Greenfield, and another son, Philip T. Hiteshew.

Top obituaries headlines
- **Phyllis M. Chait, 87, homemaker and genealogist**
- **Robert Anthony Kelly Sr., 79, automobile salesman**
- **James F. McCadden, 64, pilot, law partner, licensed captain**
- **Frances C. Wierum, 103, homemaker and pianist**
- **Deaths elsewhere**

Top baltimoresun.com headlines
- **Lawmakers, BGE promise lower increases**
- **Tagliabue to retire as NFL's chief in July**
- **Regents' lobby activity faulted**
- **Belarus election is declared invalid**
- **U.S. judge is asked to order housing for poor in suburbs**

Most e-mailed in the past 24 hours
1. **Millions face squeeze on mortgages**
2. **Fears for the farm life**
3. **Grocer a timely part of Shabbos tradition**
4. **Immigration bill draws criticism**
5. **Eileen Ambrose: Putting $743 into perspective**

Search History

STN
(HCAPLUS, INSPEC, JAPIO, USPATFULL)
3/29/05

=> d 18 1-4 abs,bib

L8 ANSWER 1 OF 4 USPATFULL on STN
AB With respect to a **liquid phase growth** method for a **silicon crystal** in which the **silicon crystal** is grown on a **substrate** by immersing the **substrate** in a **solvent** or allowing the **substrate** to contact the **solvent**, a gas containing a **raw material** and/or a **dopant** is supplied to the solvent after at least a part of the gas is decomposed by application of energy thereto. In this manner, a **liquid phase growth** method for a **silicon crystal**, the method capable of achieving continuous growth and suitable for mass production, a manufacturing method for a solar cell and a **liquid phase growth** apparatus for a **silicon crystal** are provided.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2004:86293 USPATFULL
TI **Liquid phase growth** method for **silicon crystal**, manufacturing method for solar cell and **liquid phase growth** apparatus for **silicon crystal**
IN Nishida, Shoji, Nara, JAPAN
Yoshino, Takehito, Nara, JAPAN
Iwane, Masaaki, Nara, JAPAN
Mizutani, Masaki, Nara, JAPAN
PA CANON KABUSHIKI KAISHA, Tokyo, JAPAN (non-U.S. corporation)
PI US 2004065251 A1 20040408
AI US 2003-676094 A1 20031002 (10)
PRAI JP 2002-294897 20021008
DT Utility
FS APPLICATION
LREP FITZPATRICK CELLA HARPER & SCINTO, 30 ROCKEFELLER PLAZA, NEW YORK, NY, 10112
CLMN Number of Claims: 33
ECL Exemplary Claim: 1
DRWN 5 Drawing Page(s)
LN.CNT 964
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 2 OF 4 USPATFULL on STN
AB Provided are a **liquid phase growth** method of **silicon crystal** comprising a step of injecting a source gas containing at least silicon atoms into a solvent to decompose the source gas and, simultaneously therewith, dissolving the silicon atoms into the solvent, thereby supplying the silicon atoms into the solvent, and a step of dipping or contacting a **substrate** into or with the **solvent**, thereby growing a **silicon crystal** on the substrate; and a method of producing a solar cell utilizing the aforementioned method. Also provided is a **liquid phase growth** apparatus of a **silicon crystal** comprising means for holding a solvent in which **silicon** atoms are dissolved, and means for dipping or contacting a **substrate** into or with the **solvent**, the apparatus further comprising means for injecting a source gas containing at least silicon atoms into the solvent. These provide a **liquid phase growth** method of a **silicon crystal** and a production method of a solar cell each having high volume productivity and permitting continuous growth.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:211323 USPATFULL
TI **Liquid phase growth** method of **silicon crystal**, method of producing solar, cell, and **liquid phase growth** apparatus
IN Nishida, Shoji, Kanagawa-ken, JAPAN
Nakagawa, Katsumi, Kanagawa-ken, JAPAN
Ukiyo, Noritaka, Kanagawa-ken, JAPAN
Iwane, Masaaki, Kanagawa-ken, JAPAN
PI US 2002112660 A1 20020822
AI US 2002-120357 A1 20020412 (10)
RLI Division of Ser. No. US 1998-208377, filed on 10 Dec 1998, GRANTED, Pat. No. US 6391108
PRAI JP 1997-342709 19971212
DT Utility
FS APPLICATION
LREP FITZPATRICK CELLA HARPER & SCINTO, 30 ROCKEFELLER PLAZA, NEW YORK, NY, 10112
CLMN Number of Claims: 31
ECL Exemplary Claim: 1
DRWN 4 Drawing Page(s)
LN.CNT 614
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 3 OF 4 USPATFULL on STN
AB Provided are a **liquid phase growth** method of **silicon crystal** comprising a step of injecting a source gas containing at least silicon atoms into a solvent to decompose the source gas and, simultaneously therewith, dissolving the silicon atoms into the solvent, thereby supplying the silicon atoms into the solvent, and a step of dipping or contacting a **substrate** into or with the **solvent**, thereby growing a **silicon crystal** on the substrate; and a method of producing a solar cell utilizing the aforementioned method. Also provided is a **liquid phase growth** apparatus of a **silicon crystal** comprising means for holding a solvent in which **silicon** atoms are dissolved, and means for dipping or contacting a **substrate** into or with the **solvent**, the apparatus further comprising means for injecting a source gas containing at least silicon atoms into the solvent. These provide a **liquid phase growth** method of a **silicon crystal** and a production method of a solar cell each having high volume productivity and permitting continuous growth.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2002:10790 USPATFULL
TI **LIQUID PHASE GROWTH** METHOD OF **SILICON CRYSTAL**, METHOD OF PRODUCING SOLAR CELL, AND **LIQUID PHASE GROWTH** APPARATUS
IN NISHIDA, SHOJI, HIRATSUKA-SHI, JAPAN
NAKAGAWA, KATSUMI, ATSUGI-SHI, JAPAN
UKIYO, NORITAKA, ATSUGI-SHI, JAPAN
IWANE, MASAAKI, ATSUGI-SHI, JAPAN
PI US 2002005158 A1 20020117
US 6391108 B2 20020521
AI US 1998-208377 A1 19981210 (9)
PRAI JP 1997-342709 19971212
DT Utility
FS APPLICATION
LREP FITZPATRICK CELLA HARPER & SCINTO, 30 ROCKEFELLER PLAZA, NEW YORK, NY, 10112
CLMN Number of Claims: 31
ECL Exemplary Claim: 1
DRWN 4 Drawing Page(s)

LN.CNT 614
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L8 ANSWER 4 OF 4 USPAT2 on STN
AB Provided are a **liquid phase growth** method of **silicon crystal** comprising a step of injecting a source gas containing at least silicon atoms into a solvent to decompose the source gas and, simultaneously therewith, dissolving the silicon atoms into the solvent, thereby supplying the silicon atoms into the solvent, and a step of dipping or contacting a **substrate** into or with the **solvent**, thereby growing a **silicon crystal** on the substrate; and a method of producing a solar cell utilizing the aforementioned method. Also provided is a **liquid phase growth** apparatus of a **silicon crystal** comprising means for holding a solvent in which **silicon** atoms are dissolved, and means for dipping or contacting a **substrate** into or with the **solvent**, the apparatus further comprising means for injecting a source gas containing at least silicon atoms into the solvent. These provide a **liquid phase growth** method of a **silicon crystal** and a production method of a solar cell each having high volume productivity and permitting continuous growth.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.
AN 2002:10790 USPAT2
TI **Liquid phase growth** method of **silicon crystal**, method of producing solar cell, and **liquid phase growth** apparatus
IN Nishida, Shoji, Hiratsuka, JAPAN
Nakagawa, Katsumi, Atsugi, JAPAN
Ukiyo, Noritaka, Atsugi, JAPAN
Iwane, Masaaki, Atsugi, JAPAN
PA Canon Kabushiki Kaisha, Tokyo, JAPAN (non-U.S. corporation)
PI US 6391108 B2 20020521
AI US 1998-208377 19981210 (9)
PRAI JP 1997-342709 19971212
DT Utility
FS GRANTED
EXNAM Primary Examiner: Utech, Benjamin L.; Assistant Examiner: Anderson, Matthew
LREP Fitzpatrick, Cella, Harper & Scinto
CLMN Number of Claims: 18
ECL Exemplary Claim: 1
DRWN 4 Drawing Figure(s); 4 Drawing Page(s)
LN.CNT 552
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

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(FILE 'HOME' ENTERED AT 13:31:15 ON 29 MAR 2005)

FILE 'HCAPLUS, INSPEC, JAPIO, INPADOC, USPATFULL, USPAT2' ENTERED AT 13:31:58 ON 29 MAR 2005
L1 27937 S (LPE OR LIQUID(W)PHASE(W)EPITAX? OR LIQUID(W)PHASE(W)GROW?)
L2 193444 S (SI OR SILICON)(8A)(CRYSTAL?)
L3 114745 S (SUBSTRATE#)(6A)(SOLVENT# OR LIQUID#)
L4 178185 S (DOPANT#)
L5 21222 S (DECOMPOSIT?(4A)GAS?)
L6 338325 S (RAW(W)MATERIAL#)
L7 4630569 S (METAL#)
L8 4 S L1 AND L2 AND L3 AND L4 AND L5 AND L6 AND L7